**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- MLPAK33 package (3.3 x 3.3 mm footprint)

## 3. Applications

- · High-side load switch
- Battery management
- DC-to-DC conversion
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol          | Parameter              | Conditions   |     | Min | Тур  | Max   | Unit |  |
|-----------------|------------------------|--|-----|-----|------|-------|------|--|
| $V_{DS}$        | drain-source voltage   | T <sub>j</sub> = 25 °C                                     |     | -   | -    | -30   | V    |  |
| $V_{GS}$        | gate-source voltage    |  |     | -25 | -    | 25    | V    |  |
| I <sub>D</sub>  | drain current          | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s | [1] | -   | -    | -12.8 | Α    |  |
| Static characte | Static characteristics |  |     |     |      |       |      |  |
| DOON            | rociotopoo             | $V_{GS}$ = -10 V; $I_{D}$ = -8.1 A; $T_{j}$ = 25 °C        |     | -   | 13.6 | 15.8  | mΩ   |  |
|                 |                        | $V_{GS}$ = -4.5 V; $I_D$ = -6.8 A; $T_j$ = 25 °C           |     | -   | 17.9 | 22    | mΩ   |  |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline                | Graphic symbol |
|-----|--------|-------------|-----------------------------------|----------------|
| 1   | S      | source      | 1 2 3 4                           |                |
| 2   | S      | source      |                                   |                |
| 3   | S      | source      |                                   |                |
| 4   | G      | gate        |                                   |                |
| 5   | D      | drain       |                                   |                |
| 6   | D      | drain       | Lanal                             | Ś<br>017aaa257 |
| 7   | D      | drain       | 8 7 6 5<br>MI DAK 22 (SOT 2002 4) | 31.222         |
| 8   | D      | drain       | MLPAK33 (SOT8002-1)               |                |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package |   |           |  |  |  |  |
|-------------|---------|---|-----------|--|--|--|--|
|             | Name    | Description   | Version   |  |  |  |  |
| PXP015-30QL |         | plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body | SOT8002-1 |  |  |  |  |

# 7. Marking

### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PXP015-30QL | 8AA          |

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions   |     | Min | Max   | Unit |
|------------------|-------------------------|--|-----|-----|-------|------|
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C   |     | -   | -30   | V    |
| V <sub>GS</sub>  | gate-source voltage     |  |     | -25 | 25    | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s     | [1] | -   | -12.8 | Α    |
|                  |                         | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C              | [1] | -   | -8    | Α    |
|                  |                         | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C             | [1] | -   | -5.1  | Α    |
|                  |                         | V <sub>GS</sub> = -10 V; T <sub>sp</sub> = 25 °C               |     | -   | -24.7 | Α    |
| I <sub>DM</sub>  | peak drain current      | T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs |     | -   | -43.8 | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C; t ≤ 5 s                              | [1] | -   | 4.2   | W    |
|                  |                         | T <sub>amb</sub> = 25 °C                                       | [1] | -   | 1.7   | W    |
|                  |                         | T <sub>sp</sub> = 25 °C  |     | -   | 16    | W    |
| Tj               | junction temperature    |  |     | -55 | 150   | °C   |
| T <sub>amb</sub> | ambient temperature     |  |     | -55 | 150   | °C   |
| T <sub>stg</sub> | storage temperature     |  |     | -65 | 150   | °C   |
| Source-drai      | n diode                 |  | '   | '   | '     | ,    |
| Is               | source current          | T <sub>amb</sub> = 25 °C                                       | [1] | -   | -1.7  | Α    |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

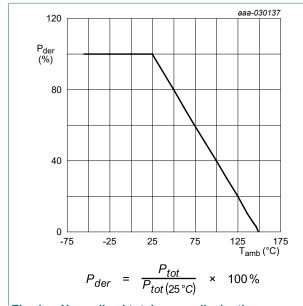


Fig. 1. Normalized total power dissipation as a function of ambient temperature

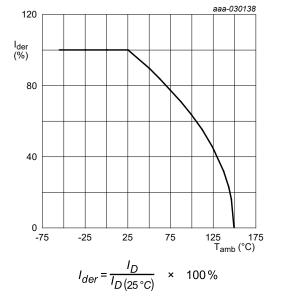


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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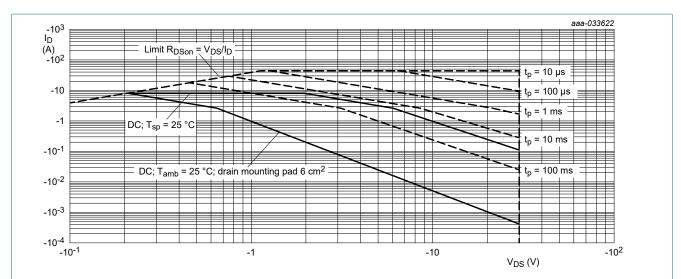


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions           |     | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| u i (j-a)             | thermal resistance from                          | in free air          | [1] | -   | 150 | 190 | K/W  |
|                       | junction to ambient                              |                      | [2] | -   | 60  | 75  | K/W  |
|                       |  | in free air; t ≤ 5 s | [2] | -   | 25  | 30  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |                      |     | -   | 4   | 8   | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

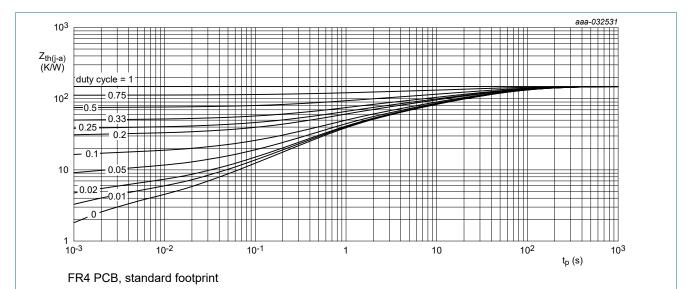


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

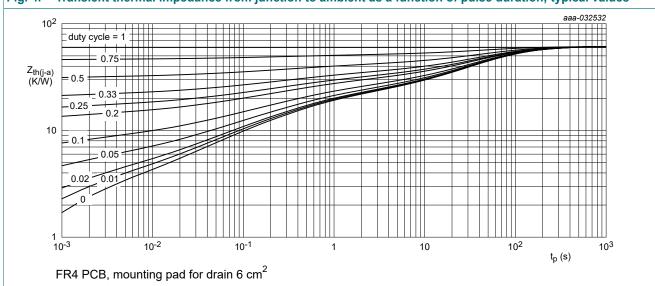


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### Table 7. Characteristics

| Symbol                 | Parameter                             | Conditions   | Min | Тур  | Max  | Unit |
|------------------------|---------------------------------------|--|-----|------|------|------|
| Static chara           | acteristics                           |  |     |      |      |      |
| V <sub>(BR)DSS</sub>   | drain-source<br>breakdown voltage     | I <sub>D</sub> = -250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C  | -30 | -    | -    | V    |
| $V_{GSth}$             | gate-source threshold voltage         | $I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                 | -1  | -1.6 | -2   | V    |
| I <sub>DSS</sub>       | drain leakage current                 | V <sub>DS</sub> = -30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | -1   | μΑ   |
| I <sub>GSS</sub>       | gate leakage current                  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | -100 | nA   |
|                        |                                       | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -    | 100  | nA   |
| R <sub>DSon</sub>      | drain-source on-state                 | $V_{GS}$ = -10 V; $I_D$ = -8.1 A; $T_j$ = 25 °C                          | -   | 13.6 | 15.8 | mΩ   |
|                        | resistance                            | $V_{GS} = -10 \text{ V}; I_D = -8.1 \text{ A}; T_j = 150 \text{ °C}$     | -   | 22   | 25.6 | mΩ   |
|                        |                                       | $V_{GS} = -4.5 \text{ V}; I_D = -6.8 \text{ A}; T_j = 25 \text{ °C}$     | -   | 17.9 | 22   | mΩ   |
| 9fs                    | forward transconductance              | $V_{DS}$ = -10 V; $I_D$ = -8.1 A; $T_j$ = 25 °C                          | -   | 22   | -    | S    |
| R <sub>G</sub>         | gate resistance                       | f = 1 MHz  | -   | 22   | -    | Ω    |
| Dynamic ch             | naracteristics                        |  |     |      |      |      |
| Q <sub>G(tot)</sub>    | total gate charge                     | $V_{DS}$ = -15 V; $I_{D}$ = -8.1 A; $V_{GS}$ = -10 V; $I_{j}$ = 25 °C    | -   | 24.6 | 36.9 | nC   |
|                        |                                       | $V_{DS} = -15 \text{ V}; I_D = -6.8 \text{ A}; V_{GS} = -4.5 \text{ V};$ | -   | 12.1 | 18.2 | nC   |
| Q <sub>GS</sub>        | gate-source charge                    | T <sub>j</sub> = 25 °C   | -   | 2.8  | -    | nC   |
| Q <sub>GS(th)</sub>    | pre-threshold gate-<br>source charge  |  | -   | 1.8  | -    | nC   |
| Q <sub>GS(th-pl)</sub> | post-threshold gate-<br>source charge |  | -   | 1    | -    | nC   |
| Q <sub>GD</sub>        | gate-drain charge                     |  | -   | 4.7  | -    | nC   |
| $V_{GSpl}$             | gate-source plateau<br>voltage        | $V_{DS}$ = -15 V; $I_D$ = -6.8 A; $T_j$ = 25 °C                          | -   | -2.4 | -    | V    |
| C <sub>iss</sub>       | input capacitance                     | V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;               | -   | 1200 | -    | pF   |
| C <sub>oss</sub>       | output capacitance                    | T <sub>j</sub> = 25 °C   | -   | 150  | -    | pF   |
| C <sub>rss</sub>       | reverse transfer capacitance          |  | -   | 120  | -    | pF   |
| t <sub>d(on)</sub>     | turn-on delay time                    | $V_{DS} = -15 \text{ V}; I_D = -6.8 \text{ A}; V_{GS} = -4.5 \text{ V};$ | -   | 4    | -    | ns   |
| t <sub>r</sub>         | rise time                             | $R_{G(ext)} = 5 \Omega; T_j = 25 °C$                                     | -   | 39   | -    | ns   |
| t <sub>d(off)</sub>    | turn-off delay time                   | 1 –  | -   | 58   | -    | ns   |
| t <sub>f</sub>         | fall time                             | 1 –  | -   | 58   | -    | ns   |
| Source-dra             | in diode                              |  | -   |      | 1    |      |
| V <sub>SD</sub>        | source-drain voltage                  | $I_S = -1.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$  | -   | -0.6 | -1.2 | V    |
| t <sub>rr</sub>        | reverse recovery time                 | I <sub>S</sub> = -1.7 A; dI <sub>S</sub> /dt = 100 A/μs;                 | -   | 14   | -    | ns   |
| Q <sub>r</sub>         | recovered charge                      | $V_{GS} = -4.5 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$   | -   | 4    | -    | nC   |
| t <sub>a</sub>         | reverse recovery rise time            |  | -   | 7    | -    | ns   |
| t <sub>b</sub>         | reverse recovery fall time            | 1  | -   | 7    | -    | ns   |

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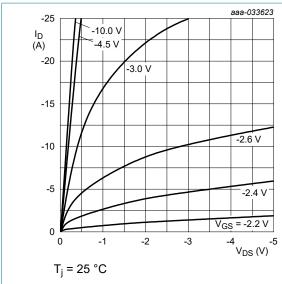


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

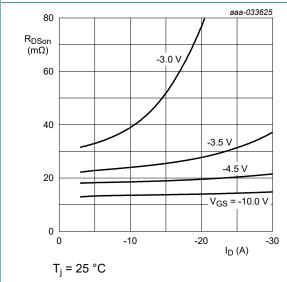


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

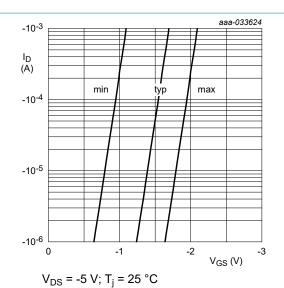


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

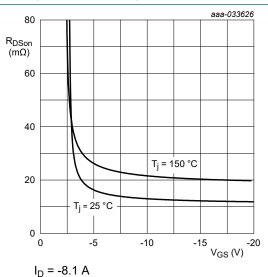


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 30 V, P-channel Trench MOSFET

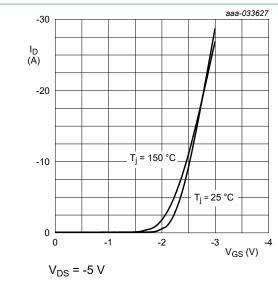


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

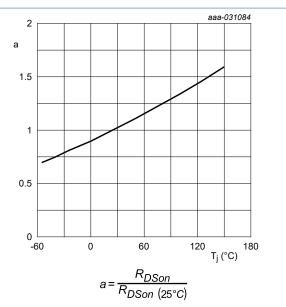


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature; typical values

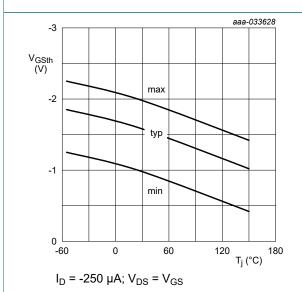


Fig. 12. Gate-source threshold voltage as a function of junction temperature

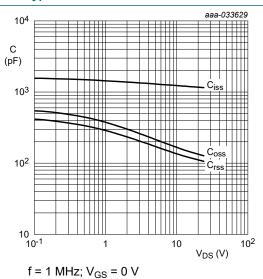


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 30 V, P-channel Trench MOSFET

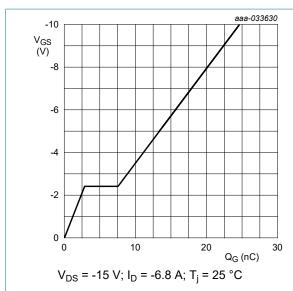


Fig. 14. Gate-source voltage as a function of gate charge; typical values

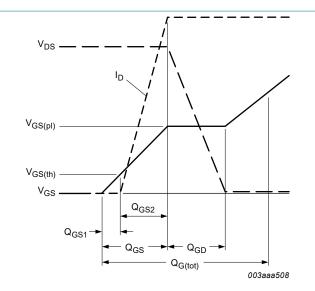


Fig. 15. Gate charge waveform definitions

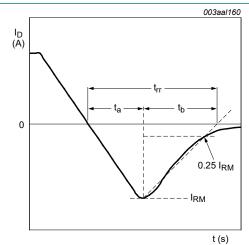


Fig. 16. Reverse recovery timing definition

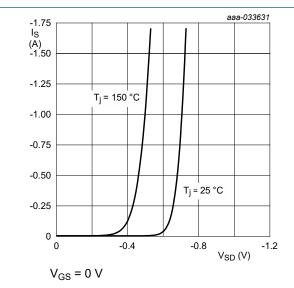
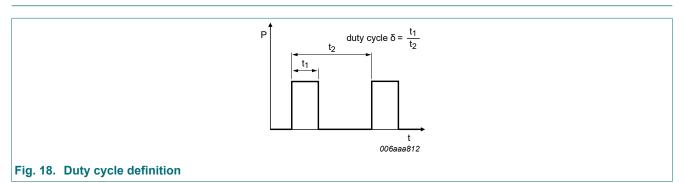


Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information



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# 12. Package outline

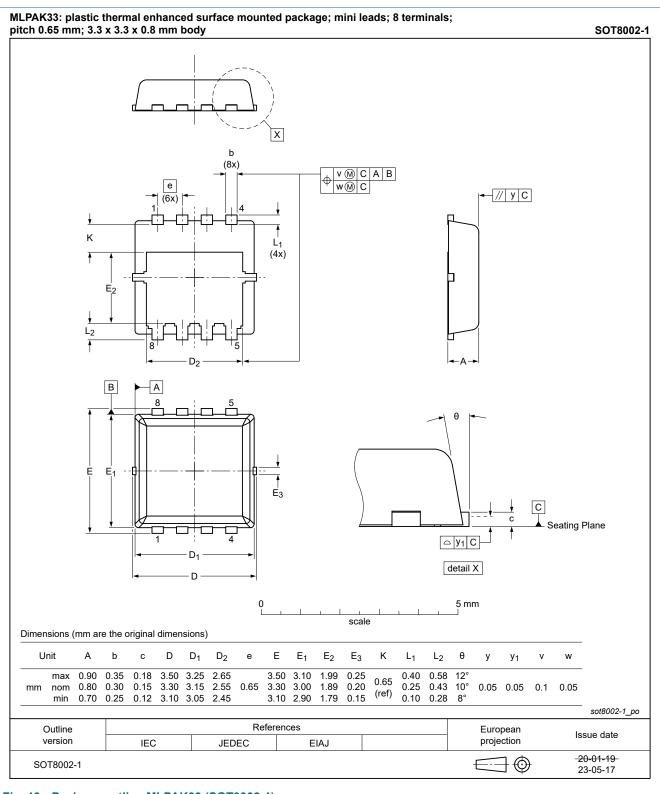
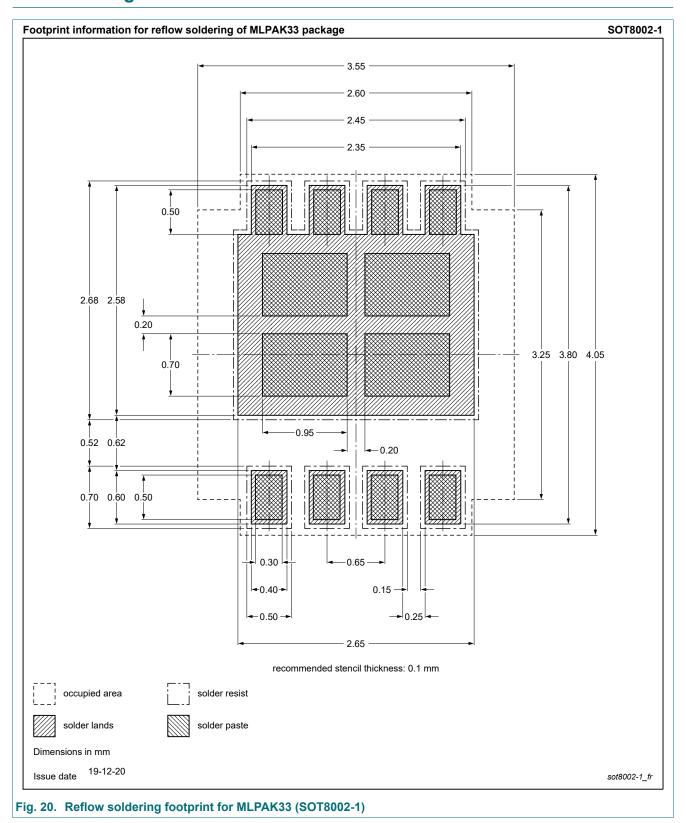


Fig. 19. Package outline MLPAK33 (SOT8002-1)

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# 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID   | Release date       | Data sheet status                         | Change notice | Supersedes      |  |  |  |  |
|-----------------|--------------------|---|---------------|-----------------|--|--|--|--|
| PXP015-30QL v.2 | 20230731           | Product data sheet                        | -             | PXP015-30QL v.1 |  |  |  |  |
| Modifications:  | Chapter "Package o | Chapter "Package outline": drawing update |               |                 |  |  |  |  |
| PXP015-30QL v.1 | 20220119           | Product data sheet                        | -             | -               |  |  |  |  |

### 30 V, P-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PXP015-30QL

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# **PXP015-30QL**

### 30 V, P-channel Trench MOSFET

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